
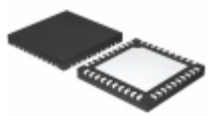



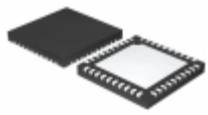

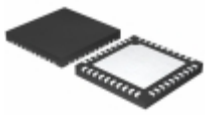

	<h2>SI3451DV-T1-E3</h2>
	<p>Hersteller-Teilenummer: SI3451DV-T1-E3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 2.8A 6-TSOP</p> <p>Datenblätter:  SI3451DV-T1-E3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 23584 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI3451DV-T1-E3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 20V 2.8A 6-TSOP
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	23584 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SOT-23-6 Thin, TSOT-23-6
Supplier Device-Gehäuse	6-TSOP
Verlustleistung (max)	1.25W (Ta), 2.1W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	2.8A (Tc)
Rds On (Max) @ Id, Vgs	115 mOhm @ 2.6A, 4.5V
VGS (th) (Max) @ Id	1.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	5.1nC @ 5V
Eingabekapazität (Ciss) (Max) @ Vds	250pF @ 10V
Verpackung	Tape & Reel (TR)



SI3451DV-T1-E3 ist neu im Original, Suche SI3451DV-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI3451DV-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI3451DV-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI3452-B02-GM Energy Micro (Silicon Labs) IC POE PSE PORT CTRLR QUAD 40QFN</p>	 <p>SI3448BDV VISHAY VISHAY sot163</p>	 <p>SI3450-GM SILICON SILICON QFN40</p>	 <p>SI3448DV-T1-E3 VISHAY SI3448DV-T1-E3 VISHAY</p>
 <p>SI3452-B01-GM Energy Micro (Silicon Labs) IC POE CONTROLLER MIDSPAN 40QFN</p>	 <p>SI3451DV-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 2.8A 6-TSOP</p>	 <p>SI3452-B01-IM Energy Micro (Silicon Labs) IC POE CONTROLLER MIDSPAN 40QFN</p>	 <p>SI3451DV-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 2.8A 6-TSOP</p>

heiße Teile

Mehr

 SI3446DV	 SI3446DV-T1	 SI3446DV-T1-E3	 SI3446DV-T1-GE3	 SI3446DV-TI-E3
 SI3447BDS	 SI3447BDV	 SI3447BDV-T1	 SI3447BDV-T1-E3	 SI3447BDV-T1-E3
 SI3447BDV-T1-GE3	 SI3447BDV-T1-GE3	 SI3447BDV-TI-GE3	 SI3447CDV-T1	 SI3447CDV-T1-E3
 SI3447CDV-T1-E3	 SI3447CDV-T1-GE3	 SI3447CDV-T1-GE3	 SI3447DV	 SI3447DV-NL
 SI3447DV-T1	 SI3447DV-T1-E3	 SI3447DV-T1-GE3	 SI3448DV	 SI3448DV-T1-E3
 SI3451DV-T1-E3	 SI3451DV-T1-GE3	 SI3451DV-T1-GE3	 SI3452DV-T1-E3	 SI3453DV-T1-GE3
 SI3453DV-T1-GE3	 SI3453DV-T5-GE3	 SI3454ADV-T1	 SI3454ADV-T1-E3	 SI3454ADV-T1-E3
 SI3454ADV-T1-GE3	 SI3454ADV-T1-GE3	 SI3454CDV-T1-GE3	 SI3454CDV-T1-GE3	 SI3454DV-NL
 SI3454DV-T1	 SI3454DV-T1-E3	 SI3455ADV-T1-E3	 SI3455ADV-T1-E3	 SI3455ADV-T1-GE3
 SI3455ADV-T1-GE3	 SI3455DV-NL	 SI3455DV-T1-E3	 SI3455DV-T1-GE3	 SI3456-C02-GU

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited